

AMENDMENTS TO THE CLAIMS

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims

Please amend original claims 1-4 with the following amended claims and add new claim 5 as follows:

1. (Amended) A method of shaping a piezoelectric material, comprising the steps of:

depositing a resist mask ~~directly to or through a film for amplification of an etching ratio to~~ on a surface of ~~an~~ a piezoelectric material;

reforming the resist mask to a predetermined thickness profile; and

dry etching the piezoelectric material together with the resist mask, wherein the piezoelectric material and the resist mask are etched at an etching rate different from each other, thereby shaping the surface of the piezoelectric material ~~being shaped to~~ a three-dimensional configuration corresponding to the thickness profile of the resist mask.

2. (Original) The method defined in claim 1, wherein the thickness profile is given to the resist mask by patterning and melting a masking material applied to the surface of the piezoelectric material.

3. (Original) The method defined in claim 1, wherein the thickness profile is given to the resist mask by pressing a precision stamp onto a masking material applied to the surface of the piezoelectric material.

4. (Amended) The method defined in ~~either one of claims 1 to 3~~ claim 1, wherein the dry etching is started with a less selectively reactive gas for reforming the resist mask to a predetermined thickness profile and then continued with an etching gas having high selective reactivity to the piezoelectric material.

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5. (New) The method defined in claim 1, further comprising the step of depositing a film on the surface of the piezoelectric material prior to depositing the resist mask.